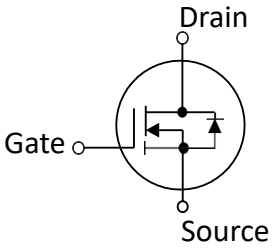
## *30V N-Channel MOSFET*

- Advanced Split Gate Device Design and Processes
- High Reliability Capability
- Sampled CP Probing

**SYMBOL**



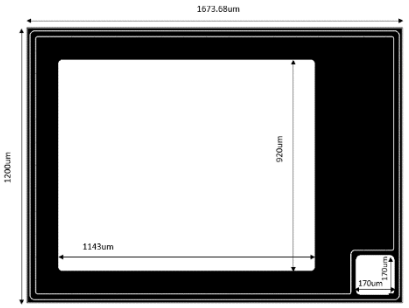

## Electrical Characteristics in C/P Test ($T_J$ at 25 ℃)

| Symbol | Parameter | Min. | Typ. | Max. | Unit | Test Condition |
|---|---|---|---|---|---|---|
| $V_{(BR)DSS}$ | Drain-Source Breakdown Voltage | 30 | — | — | V | $V_{GS}$ =0V, $I_D$ =250μA |
| $R_{DS(ON)}$ | Static Drain-Source On-Resistance | — | 2.6 | 3.4 | mΩ | $V_{GS}$ =10V, $I_D$ =1A(1) |
| $R_{DS(ON)}$ | Static Drain-Source On-Resistance | — | 2.9 | 3.8 | mΩ | $V_{GS}$ =4.5V, $I_D$ =1A(1) |
| $V_{GS\ (th)}$ | Gate Threshold Voltage | 1.35 | — | 2.3 | V | $V_{DS}$ =$V_{GS}$, $I_D$ =250μA |
| $I_{DSS}$ | Drain-to-Source Leakage Current | — | — | 1 | μA | $V_{DS}$ =30V, $V_{GS}$ =0V |
| $I_{GSS}$ | Gate-to-Source Leakage Current | -100 | — | 100 | nA | $V_{DS}$ =0V, $V_{GS}$ =±20V |
| $T_J$, $T_{STG}$ | Operating and Storage Temperature | -55℃ to 150℃ Max. | | | | |

## Mechanical Data

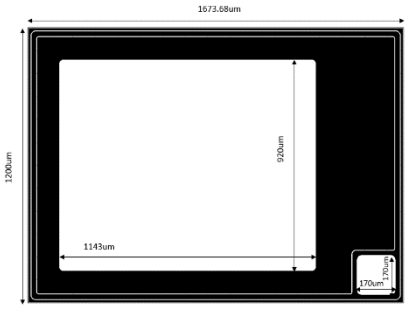
| | |
|---|---|
| Chip Size(2) | 1674 μm X 1200 μm |
| Gate Pad Size | 170 μm X 170 μm |
| Source Pad Size | 1143 μm X 920 μm |
| Scribe Line Width | 60 μm |
| Wafer Thickness | 100 μm |
| Wafer Diameter | 200 mm |
| Gross Die | 13150 EA |
| Source Metallization | Ti-NiV-Ag / 1-3-1.5kA |
| Drain Metallization | Ti-Ni-Ag |
| Passivation | Polyimide |
| Recommended Storage Environment | Store in original container, in dry nitrogen, 6 months at ambient temperature of 23°C ± 3°C |

## Die Drawing

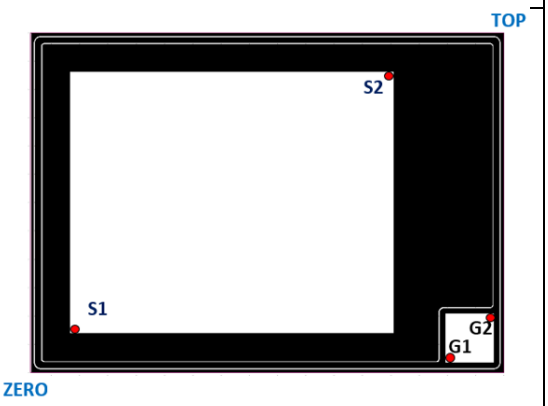



(1) Pulse Width tp = < 1 mS, Duty Cycle < 2%.

(2) Chip size not include scribe line.

| Specific Assembly Information Bill of Material (BOM) | | Die Drawing |
|---|---|---|
| Package Type | DFN5*6 |  |
| Die Attach Method | Soft solder | |
| Soft Solder Composition | Pb,Sn,Ag | |
| Gate Wire Bonding | Cu, 2 mil x1 | |
| Source Wire Bonding | Cu, 2 mil x 10 | |
| Molding Compound Manufacturer | G700HF | |
| Solder Plating Composition | Pure Tin | |



| Position | | | Bonding Diagram Top View |
|---|---|---|---|
| | X (μm) | Y (μm) |  |
| ZERO | 0 | 0 | |
| TOP | 1673.7 | 1200 | |
| S1 | 140 | 140 | |
| S2 | 1283 | 1060 | |
| G1 | 1467.1 | 36.7 | |
| G2 | 1637.1 | 206.7 | |

## Electrical Characteristics in F/T Test ($T_J$ at 25 ℃)

| Symbol | Parameter | Min. | Typ. | Max. | Unit | Test Condition |
|---|---|---|---|---|---|---|
| $I_{DSS}$ | Drain-to-Source Leakage Current | — | — | 1 | μA | $V_{DS}$ =30V, $V_{GS}$ =0V |
| $I_{GSSF}$ | Gate-to-Source Leakage Current | — | — | 100 | nA | $V_{DS}$ =0V, $V_{GS}$ =+20V |
| $I_{GSSR}$ | Gate-to-Source Leakage Current | -100 | — | — | nA | $V_{DS}$ =0V, $V_{GS}$ =-20V |
| $BV_{DSS}$ | Drain-Source Breakdown Voltage | 30 | — | — | V | $V_{GS}$ =0V, $I_D$ =250μA |
| $BV_{DSS}$ | Drain-Source Breakdown Voltage | 30 | — | — | V | $V_{GS}$ =0V, $I_D$ =1mA |
| $R_{DS(ON)}$ | Static Drain-Source On-Resistance | — | — | 5 | mΩ | $V_{GS}$ =10V, $I_D$ =19A |
| $R_{DS(ON)}$ | Static Drain-Source On-Resistance | — | — | 7 | mΩ | $V_{GS}$ =4.5V, $I_D$ =19A |
| $V_{GS\ (th)}$ | Gate Threshold Voltage | 1.35 | — | 2.3 | V | $V_{DS}$ =$V_{GS}$, $I_D$ =250μA |
| $V_{SD}$ | Body Diode Forward Voltage | — | — | 1.2 | V | $V_{GS}$ =0V, $I_{SD}$ =19A |
| $I_{AS}$ | Avalanche Current | | | | A | $V_{DD}$=25V, $V_{GS}$=10V, $R_G$=25Ω, L=0.1mH |
| $T_J$, $T_{STG}$ | Operating and Storage Temperature | -55 | — | 150 | ℃ | |

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